

## STM1645-30

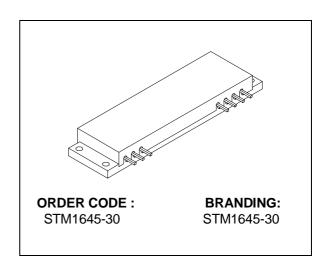
# RF POWER MODULE SATELLITE COMMUNICATION APPLICATIONS

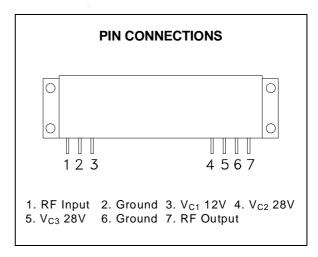
- CLASS C SATELLITE COMMUNICATIONS AMPLIFIER
- 1625- 1665 MHz
- 12/28 VOLTS
- INPUT/OUTPUT 50 OHMS
- Pout = 30 W MIN.
- GAIN = 34.8 dB MIN.

## **DESCRIPTION**

The STM1645-30 hybrid RF Power Module is designed for high power satellite communication applications in the 1.6 GHz frequency range.

High  $f_T$ , gold metallized silicon microwave power devices, optimized for use in STM1645-30, are employed to provide high gain and efficiency while ensuring excellent reliability.





## **ABSOLUTE MAXIMUM RATINGS** (Tcase = 25 °C)

Symbol	Parameter	Value	Unit
V	DC Supply Voltage	30	Vdc
PiN	RF Input Power (P <sub>OUT</sub> ≤ 30 W)	20	mW
T <sub>STG</sub>	Storage Temperature Range	- 40 to + 100	°C
T <sub>C</sub>	Operating Case Temperature	-35 to + 70	°C

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## **ELECTRICAL SPECIFICATION** ( $T_{case} = 25$ $^{o}C$ , $V_{C1*} = 12$ V; $V_{C2}$ , $V_{C3} = 28$ V)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max	Unit
BW	Frequency Range		1625		1665	MHz
P <sub>OUT</sub>	Power Output	P <sub>IN</sub> ≤ 10 W	30	35	40	W
G <sub>P</sub>	Power Gain	P <sub>OUT</sub> = 30 W	34.8	35.5		dB
η	Efficiency	P <sub>OUT</sub> = 30 W	35			%
Z <sub>IN</sub>	Input Impedance	$P_{OUT} = 30 \text{ W}$ $Z_G, Z_L = 50 \Omega$		1.5:1	2:1	VSWR
Н	Harmonics	P <sub>OUT</sub> = 30 W reference		-45	-40	dB
	ΔP <sub>OUT</sub> vs T <sub>CASE</sub>	$T_C = -35^{\circ}C \text{ to } +70^{\circ}C @ P_{IN} = 10\text{mW}$			2	dB
	ΔP <sub>OUT</sub> vs Frequency	f = 1625 - 1665 MHz			1	dB
	Load Mismatch	VSWR = 10:1 V = 28 Vdc P <sub>OUT</sub> = 30 W	No Degradation in Output Power			
	P <sub>OUT</sub> Control Range	P <sub>OUT</sub> = 30 W	8	10		dB
	Stability	P <sub>OUT</sub> = 5 to 30 W** Load VSWR = 3:1 any phase	All Spurious Outputs More Than 60 dB Below Carrier			

REF. 1015506I

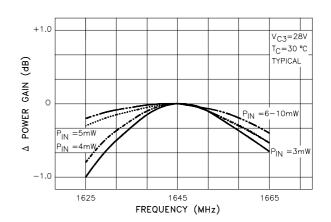
Note:
\* V<sub>C1</sub> = 12 V regulated ±1%
\*\* P<sub>OUT</sub> adjusted by varying V<sub>C3</sub>

## TYPICAL PERFORMANCE

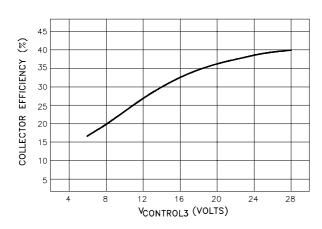
## Power Output vs Frequency and Power Input

# 45 40 P<sub>IN</sub> =6-10mW P<sub>IN</sub> =6-10mW P<sub>IN</sub> =5mW P<sub>IN</sub> =4mW P<sub>IN</sub> =4mW P<sub>IN</sub> =3mW T<sub>C</sub>=30 °C TYPICAL 1625 1645 FREQUENCY (MHz)

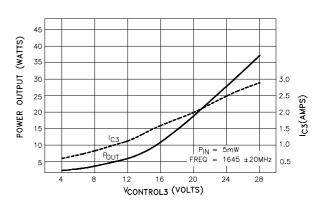
## Power Gain vs Frequency and Power Input



## VCONTROL vs Collector Efficiency



## VCONTROL vs Power Output and Ic3 (Typical)



## **APPLICATIONS RECOMMENDATIONS**

## **OPERATION LIMITS**

The STM1645-30 power module should never be operated under any condition which exceeds the Absolute Maximum Ratings presented on this data sheet. Nor should the module be operated continuously at any of the specified maximum ratings. If the module is to be subjected to one or more of the maximum rating conditions, care must be taken to monitor other parameters which may be affected.

## **MODULE MOUNTING**

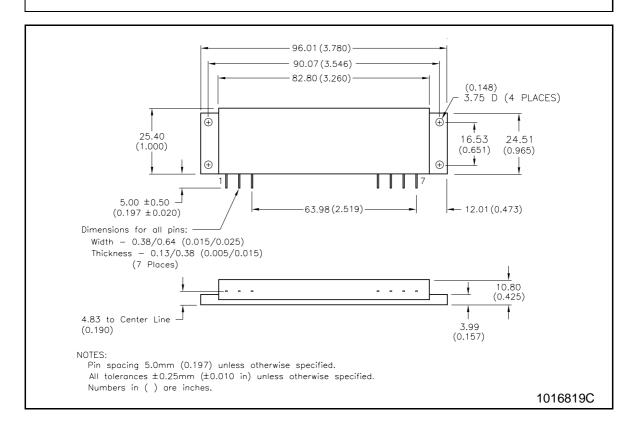
To insure adequate thermal transfer from the module to the heatsink, it is recommended that a satisfactory thermal compound such as Dow Corning 340, Wakefield 120-2 or equivalent be applied between the module flange and the heatsink.

The heatsink mounting surface under the module should be flat to within  $\pm\,0.05$  mm ( $\pm\,0.002$  lnch). The module should be mounted to the heatsink using 3.5 mm (or 6-32) or equivalent screws torqued to 5-6 Kg-cm (4-6 in-lb).

The module leads should be attached to equipment PC board using 180°C solder applied to leads with a properly grounded soldering iron tip, not to exceed 195 °C, applied a minimum of 2 mm (0.080 inch) from the body of the module for a duration not to exceed 15 seconds per lead. It is imperative that no other portion of the module, other than the leads, be subjected to temperature in excess of 100 °C (maximum storage temperature), for any period of time, as the plastic moulded cover, internal components and sealing adhesives may be advertisely affected by such conditions.

Due to the construction techniques and materials used within the module, reflow soldering of the flange heatsink or leads, is not recommended.

## **H160 MECHANICAL DATA**



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